

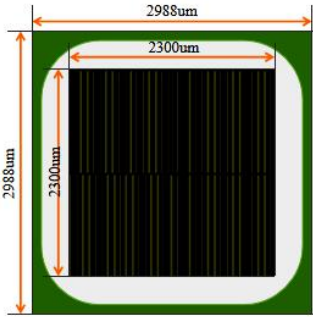
**High Voltage Trench Schottky Diode****FEATURES**

- Trench MOS Schottky technology
- Die in 6" Wafer Form
- 100V, 15A*
- $V_F=0.69V(\text{typ.})^{**}$

Electrical Characteristics (T_j=25°C)

| Parameter | Description | Min. | Typ. | Max. | Unit | Test Condition |
|---|---|--------------------|------|------|------|------------------------|
| V _{RRM} | Maximum repetitive peak reverse voltage | 125 | 136 | — | V | I _R = 500μA |
| V _F | Static Forward Voltage | — | 0.37 | 0.43 | V | I _F = 1A |
| | | — | 0.55 | 0.65 | V | I _F = 8A |
| | | — | 0.69 | 0.76 | V | I _F = 15A |
| I _R ^{***} | Cathode-To-Anode Leakage Current | — | 18 | 50 | μA | V _R = 120V |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55°C to 150°C Max | | | | |
| *** Pulse width < 300 uS, Duty cycle < 2% | | | | | | |

Mechanical Data

| | | | |
|---------------------------------|--|-----------------|--|
| Die Size | 3048×3048 | μm ² | CHIP DRAWING (Scribe Line is Excluded)  |
| Source Pad Size | 2300× 2300 | μm ² | |
| Scribe Line Size | 60 | μm | |
| Wafer Diameter | 6 | in | |
| Wafer Thickness | 250 | μm | |
| Estimated Gross Die | 1699(Yield>97%) | | |
| Anode Metal Thickness | AlSiCu(5.5μm) | | |
| Cathode Metal Thickness | Ti\Ni\Ag (0.2μm\0.3μm\2μm) | | |
| Recommended Storage Environment | Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C±3°C > | | |

* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

** Electrical characteristics are reported for the bare die. Variations in customer packaging materials, dimensions and processes may affect parametric performance.